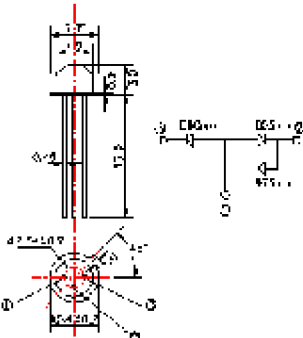


L660/805/975-40D00 Multi-wavelength LED

L660/805/975-40D00 consists of a GaAlAs LED 660nm, 805nm and GaAs LED 975nm mounted on TO-18 stem with an epoxy lens.

†Specifications

1)Product No.	Multi-wavelength LED Lamp	
2)type No.	L660/805/975-40D00	
3)Chip		
(1)Chip material	GaAlAs and GaAs	
(2)Peak wavelength	660, 805, 975nm	
4)Package		
(1)stem type	TO-18 stem	
(2)Lens	Clear epoxy resin	

†Absolute Maximum Ratings Ta=25 °C

Item	Symbol	Maximum Rated Value			Unit
		660	805	975	
Power Dissipation	PD	120	170	140	mW
Forward Current	IF	50	100	100	mA
Reverse Voltage	VR	5			V
Operating Temperature	TOPR	-20~+85			°C
Storage Temperature	TSTG	-30~+95			°C
Soldering Temperature	TSOL	260			°C

†Electro-Optical Characteristics (Ta=25 °C)

Item		Symbol	Condition	Minimum	Typical	Maximum	Unit
Forward Voltage	660nm	VF	IF=20mA		1.9	2.3	V
	805nm				1.4	1.6	
	975nm				1.2	1.4	
Reverse Current	660nm	IR	VR=5V			10	uA
	805nm						
	975nm						
Total Radiation Power	660nm	Po	IF=20mA	2.5	3.5		mW
	805nm			3.5	6.0		
	975nm			1.0	2.0		
Peak Wavelength	660nm	λP	IF=20mA	650	660	670	nm
	805nm			795	805	815	
	975nm			960	975	985	
Half Width	660nm	Δλ	IF=20mA		20		nm
	805nm				30		
	975nm				55		

Total Radiated Power is measured by Photodyne #500

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